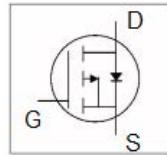
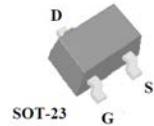


- Simple Drive Requirement
- Small Package Outline
- Surface Mount Device
- RoHS Compliant & Halogen-Free



BVDSS	-30V
RDS(ON)typ	47mΩ
ID	-4.2A



Description

KE8301 is from Kingeavy innovated design and silicon process technology to achieve the lowest possible on- resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-30	V
VGS	Gate-Source Voltage	± 12	V
$I_D @ T_A=25^\circ\text{C}$	Drain Current, $V_{GS} @ 10\text{V}_3$	-4.2	A
$I_D @ T_A=70^\circ\text{C}$	Drain Current, $V_{GS} @ 10\text{V}_3$	-3.5	A
I_{DM}	Pulsed Drain Current ¹	-25	A
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	125	$^\circ\text{C}/\text{W}$

Electrical Characteristics@ $T_j=25\text{ }^\circ\text{C}$ (unless otherwise specified)

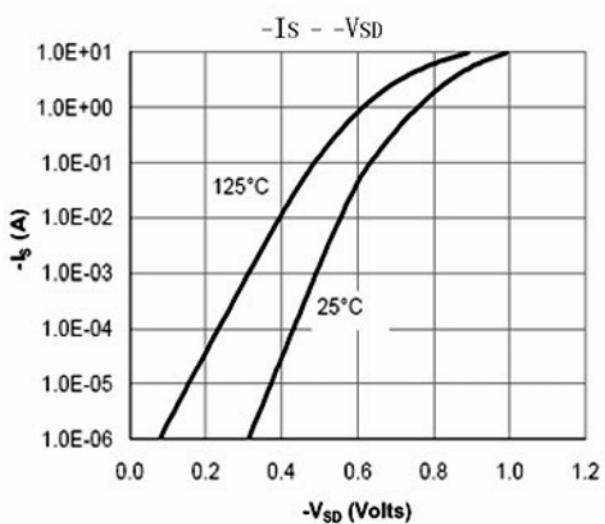
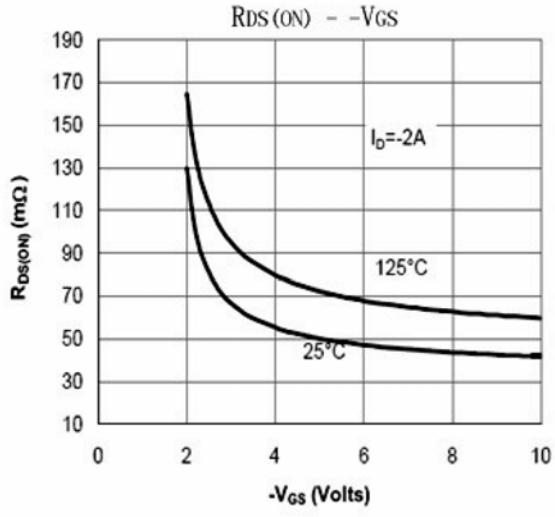
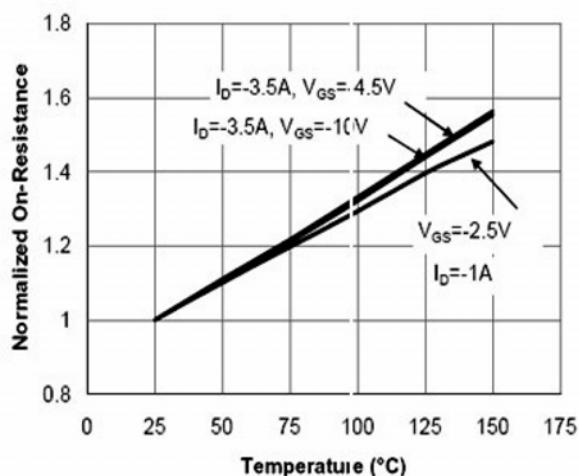
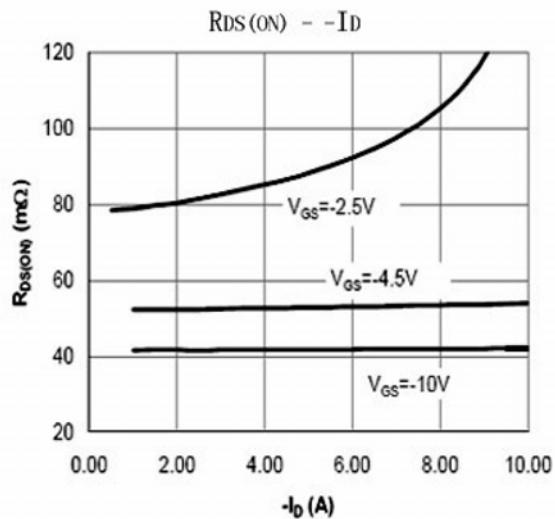
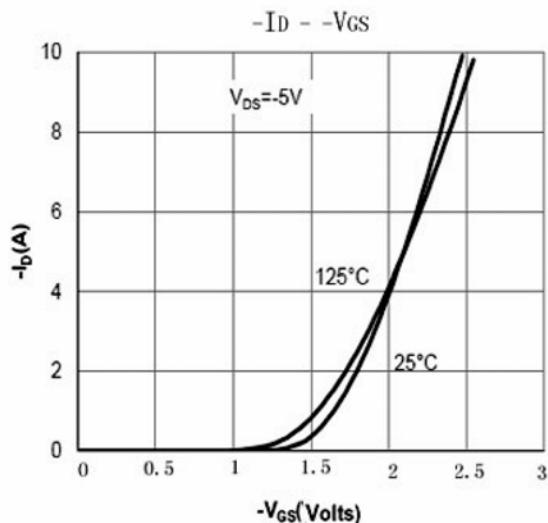
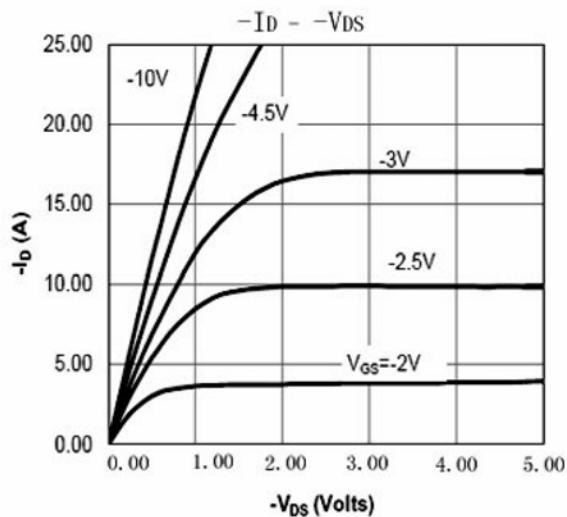
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$\text{VGS}=0\text{V}, \text{ID}=250\mu\text{A}$	-30	-	-	V
$\text{RDS}(\text{ON})$	Static Drain-Source On-Resistance	$\text{VGS}=10\text{V}, \text{ID}=-5.3\text{A}$	-	47	58	$\text{m}\Omega$
		$\text{VGS}=-4.5\text{V}, \text{ID}=-3\text{A}$	-	58	65	$\text{m}\Omega$
		$\text{VGS}=-2.5\text{V}, \text{ID}=-1\text{A}$	-	75	85	$\text{m}\Omega$
$\text{V}_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$\text{VDS}=\text{VGS}, \text{ID}=250\mu\text{A}$	-0.7	-0.9	-1.2	V
g_{fs}	Forward Transconductance	$\text{VDS}=5\text{V}, \text{ID}=-4\text{A}$	-	8	-	S
I_{DSS}	Drain-Source Leakage Current	$\text{VDS}=24\text{V}, \text{VGS}=0\text{V}$	-	-	-1	μA
I_{GSS}	Gate-Source Leakage	$\text{VGS}=\pm 12\text{V}, \text{VDS}=0\text{V}$	-	-	± 100	nA
Q_g	Total Gate Charge	$\text{ID}=4\text{A}$	-	11	20	nC
Q_{gs}	Gate-Source Charge		-	2	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge		-	4	-	nC
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$\text{VDS}=-15\text{V}$ $\text{ID}=4\text{A}$	-	6.3	-	ns
t_r	Rise Time		-	3.2	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time		-	38.2	-	ns
t_f	Fall Time	$\text{RG}=3.3\Omega$ $\text{VGS}=-10\text{V}$	-	12	-	ns
C_{iss}	Input Capacitance		-	957	-	pF
C_{oss}	Output Capacitance		-	115	-	pF
Crss	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	77	-	pF

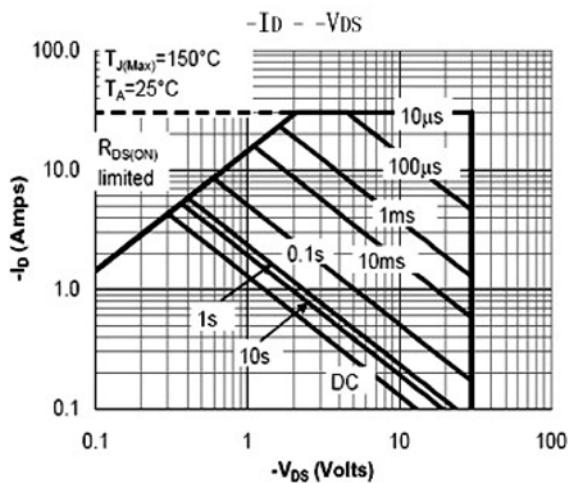
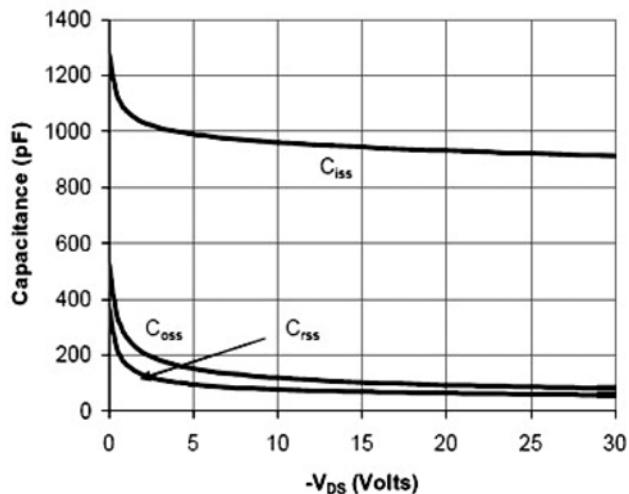
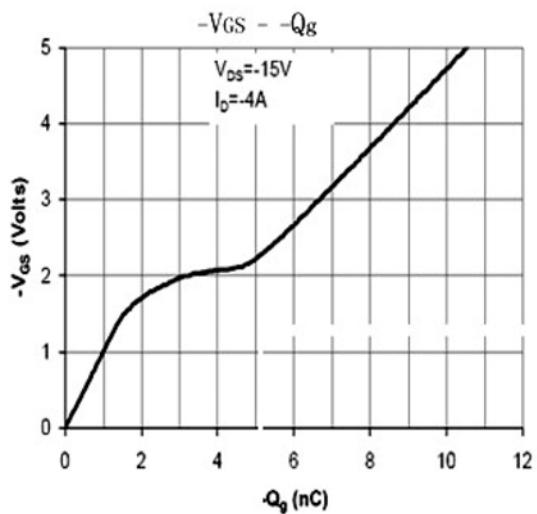
Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$\text{Is}=1\text{A}, \text{VGS}=0\text{V}$	-	-	-1	V

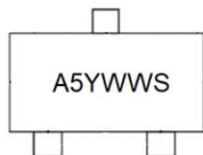
Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² 2oz copper pad of FR4 board, $t \leq 10\text{sec}$; $300^\circ\text{C}/\text{W}$ when mounted on min. copper pad.



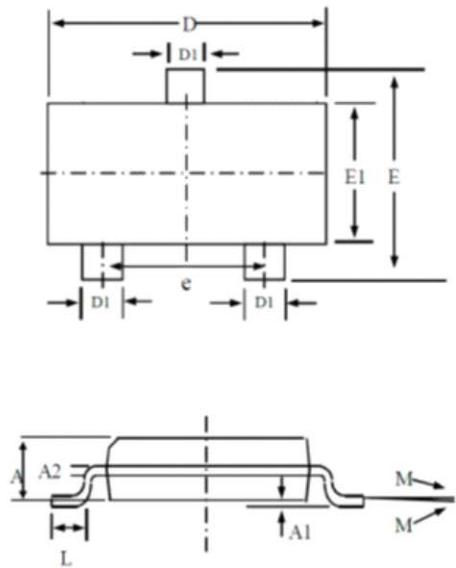


Marking Information



Package	SOT-23	
A5	PN code	KE8301T0U
Y	Year	F=2020 , G=2021,
WW	Weeks	Ex. 2020 3/2=10week, 4/6=15week
S	Serial	Serial No.

Package Outline : SOT-23



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	0.80	1.00	1.20
A1	0.00	—	0.10
A2	0.05	—	0.20
D1	0.30	0.40	0.50
e	1.80	1.90	2.00
D	2.80	2.90	3.10
E	2.10	2.40	2.70
E1	1.20	1.30	1.40
M	0°	5°	10°
L	0.20	—	0.60

1. All Dimension Are In Millimeters.

2. Dimension Does Not Include Mold Protrusions.